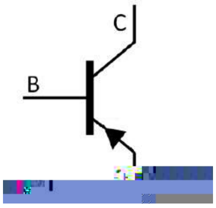
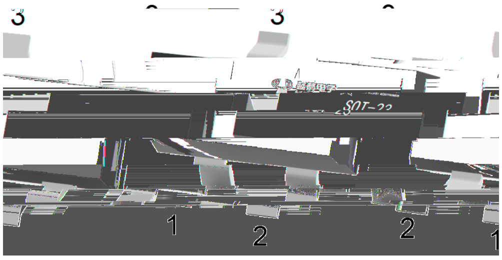
9 5 : .> / / x 6 4 6 ! - } â 'ož Silicon PNP transistor in a SOT-23 Plastic Package.

(8 9 3 7 ; m k … ` ' +) 7 ö Õ ä U ´ Å } L k —)í D }ož
Complementary pair with BRS8050MQ, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

9 ä y Ý è k á V ñ • } Lož
Power amplifier applications, Meet the stringent requirements of automotive applications.



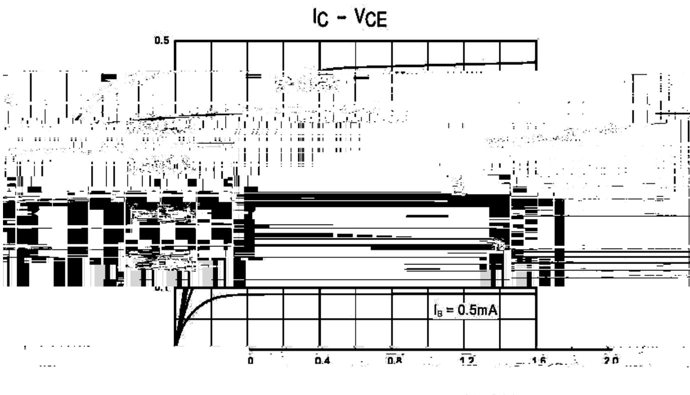


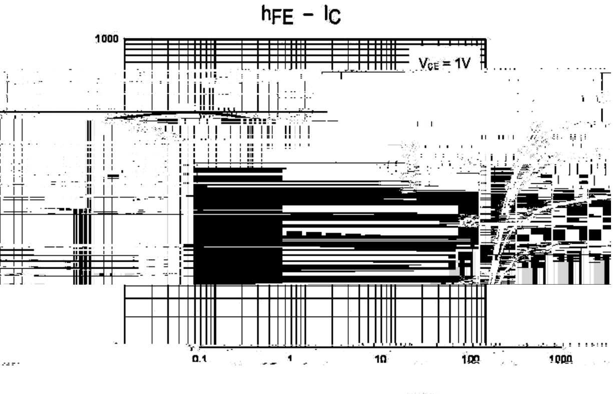
PIN1 y

@ ƒ Parameter	… Z Symbol	ƒ › Rating	% y Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-25	V
Emitter to Base Voltage	V_{EBO}	-6.0	V
Collector Current	I_C	-800	mA
Base Current	I_B	-200	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-65 150	

@ ƒ Parameter	… Z Symbol	y ¡ Ú ^ Test Conditions	Â 4 › Min	Á º › Typ	Â Ý › Max	% y Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-0.1mA I_E=0	-40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-2.0mA I_B=0	-25			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=-0.1mA I_C=0	-6.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-35V I_E=0			-0.1	A
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-6.0V I_C=0			-0.1	A

Ô ? d • Ž ¢ / Electrical Characteristic Curve





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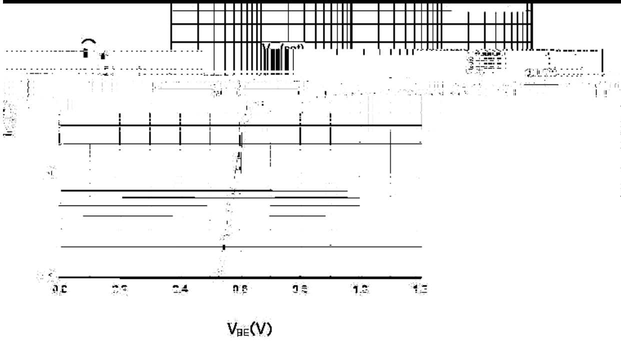

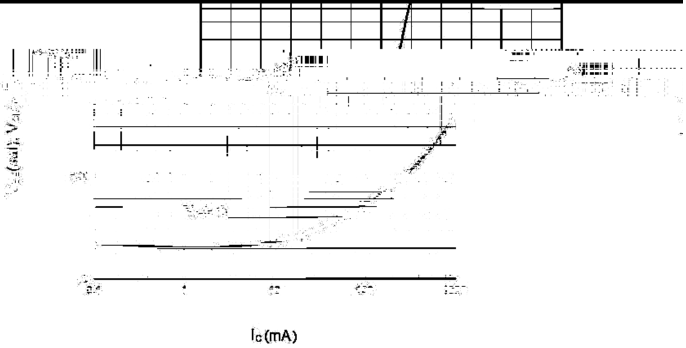

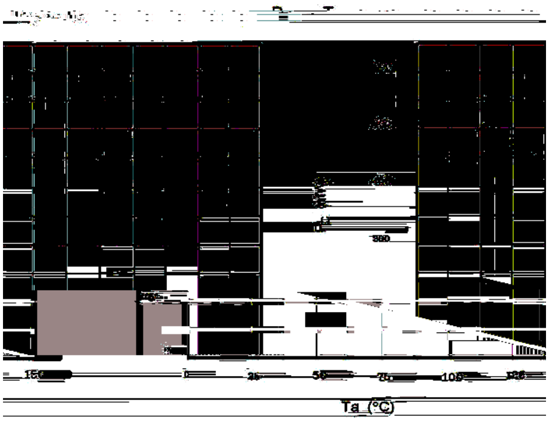

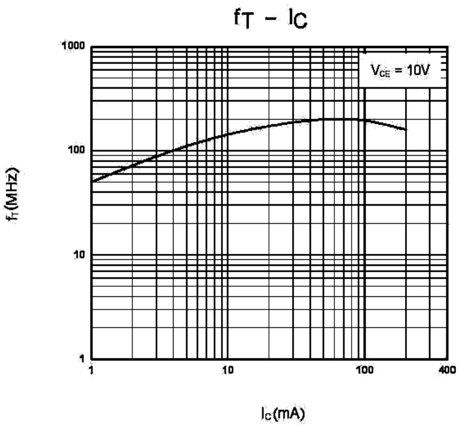

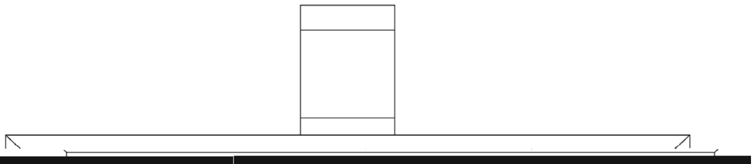

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šWD t…•Ž¢ (x/) / :KSVKXGZ[XK 6XULORK LUX /8 8KLRU] 9URJKXOTM 6

ª¢y

1o•Ä½“† 150 ½200 -kž• 60 ½120sec;

2o•Q›“† 255 r5 -kž•4Ò 5 r0.5sec;

3o•D Nòi Ò0,† 2 ½10 - /sec.

Note:

1.Preheating:150~200 - , Time:60~120sec.

2.Peak Temp.:255 r5 - , Duration:5 r0.5sec.

3. Cooling Speed: 2~10 - /sec.

ÂD /Cãp¯»] / Resistance to Soldering Heat Test Conditions

“†y 260 r5 - ž•y 10 r1 sec.

Temp.:260±5 Time:10±1 sec

GPá / Packaging SPEC.

2& x / REEL

Package Type 7>û˜E	Units ;>û¦H	Dimension ;>ûp. (unit Æmm^3)
	Units/Reel / --	